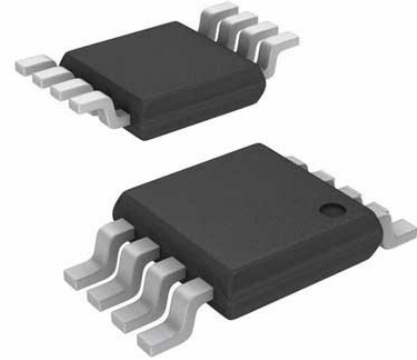


RF Amplifier InGaP HBT pow amp SMT, 5 - 7 GHz

Manufacturers	Analog Devices, Inc
Package/Case	MSOP8
Product Type	RF Amplifiers
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for HMC407MS8G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

The HMC407MS8G & HMC407MS8GE are high efficiency GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC Power amplifiers which operate between 5 and 7 GHz. The amplifier requires no external matching to achieve operation and is thus truly 50 Ohm matched at input and output. The amplifier is packaged in a low cost, surface mount 8 leaded package with an exposed base for improved RF and thermal performance. The amplifier provides 15 dB of gain, +29 dBm of saturated power at 28% PAE from a +5V supply voltage. Power down capability is available to conserve current consumption when the amplifier is not in use.

Applications

UNII

HiperLAN

Features

Gain: 15 dB

Saturated Power: +29 dBm

28% PAE

Supply Voltage: +5V

Power Down Capability

No External Matching Required

Application

UNII

HiperLAN

Related Products



[HMC3653LP3BE](#)

Analog Devices, Inc
QFN-12



[HMC253AQS24](#)

Analog Devices, Inc
24-SSOP (0.154, 3.90mm Width)



[HMC358MS8GE](#)

Analog Devices, Inc
MSOP-8



[HMC453ST89E](#)

Analog Devices, Inc
ST89E



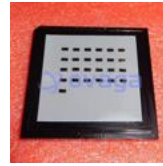
[HMC441LP3E](#)

Analog Devices, Inc
QFN-16



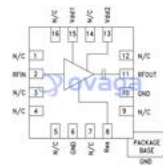
[HMC948LP3E](#)

Analog Devices, Inc
LP3



[HMC490](#)

Analog Devices, Inc
SMD



[HMC618ALP3E](#)

Analog Devices, Inc
QFN-16